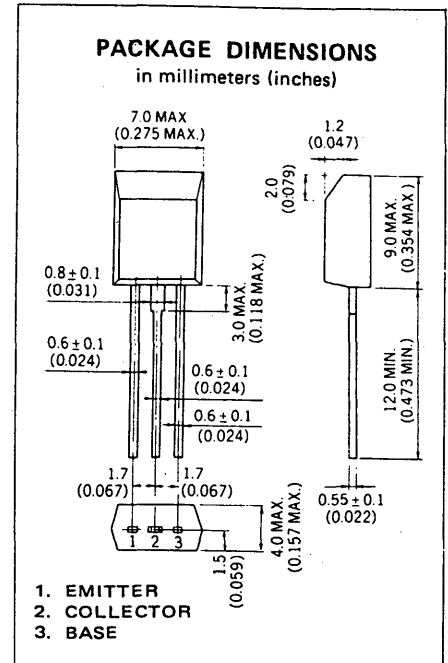


DESCRIPTION The 2SB734 is designed for use in driver and output stages of audio frequency amplifiers.

- FEATURES**
- High Total Power Dissipation P_T : 1.0 W ($T_a=25^\circ\text{C}$)
 - High Voltage V_{CE0} : -50 V MIN.
 - Complementary to the NEC 2SD774 NPN Transistor.

ABSOLUTE MAXIMUM RATINGS

- Maximum Temperatures
- Storage Temperature -55 to +150 °C
 - Junction Temperature 150 °C Maximum
- Maximum Power Dissipation ($T_a=25^\circ\text{C}$)
- Total Power Dissipation 1.0 W
- Maximum Voltages and Current ($T_a=25^\circ\text{C}$)
- V_{CBO} Collector to Base Voltage -60 V
 - V_{CEO} Collector to Emitter Voltage -50 V
 - V_{EBO} Emitter to Base Voltage -6.0 V
 - I_C Collector Current -1.0 A



ELECTRICAL CHARACTERISTICS ($T_a=25^\circ\text{C}$)

SYMBOL	CHARACTERISTIC	MIN.	TYP.	MAX.	UNIT	TEST CONDITIONS
h_{FE1}	DC Current Gain	135	250	600	—	$V_{CE}=-2.0\text{ V}$, $I_C=-100\text{ mA}$
h_{FE2}	DC Current Gain	40			—	$V_{CE}=-1.0\text{ V}$, $I_C=-1.0\text{ A}$
f_T	Gain Bandwidth Product	50	80		MHz	$V_{CE}=-2.0\text{ V}$, $I_E=10\text{ mA}$
C_{ob}	Output Capacitance		23	50	pF	$V_{CB}=-10\text{ V}$, $I_E=0$, $f=1.0\text{ MHz}$
I_{CBO}	Collector Cutoff Current			-100	nA	$V_{CB}=-50\text{ V}$, $I_E=0$
I_{EBO}	Emitter Cutoff Current			-100	nA	$V_{EB}=-6.0\text{ V}$, $I_C=0$
V_{BE}	Base to Emitter Voltage	-0.55	-0.60	-0.65	V	$V_{CE}=-6.0\text{ V}$, $I_C=-50\text{ mA}$
$V_{CE(sat)}$	Collector Saturation Voltage		-0.35	-0.60	V	$I_C=-1.0\text{ A}$, $I_B=-50\text{ mA}$
$V_{BE(sat)}$	Base Saturation Voltage		-0.94	-1.20	V	$I_C=-1.0\text{ A}$, $I_B=-50\text{ mA}$

Classification of h_{FE1}

Rank	L ₂	K ₃	K ₄	U ₄	U ₅
Range	135 - 270	200 - 320	250 - 400	300 - 480	360 - 600

Test Conditions : $V_{CE}=-2.0\text{ V}$, $I_C=-100\text{ mA}$

TYPICAL CHARACTERISTICS (Ta=25 °C)

